



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of: **YAMAJI, Shigeo**

Serial No.: **09/730,588**

Group Art Unit: **2836**

Examiner: **Isabel Rodriguez**

Filed: **December 7, 2000**

P.T.O. Confirmation No.: **9635**

For: **CONTROL CIRCUIT FOR SEMICONDUCTOR DEVICE WITH OVERHEAT PROTECTING FUNCTION**

**AMENDMENT UNDER 37 CFR §1.111**

Commissioner for Patents  
Washington, D.C. 20231

Date: **December 6, 2002**

Sir:

In response to the Office Action dated September 6, 2002, please amend the above-identified application as follows:

**IN THE SPECIFICATION:**

Please amend the specification as indicated:

**Replace the paragraph on page 2, starting with line 18 with the following:**

A' On the other hand, when an abnormality such as the short of the load 4 arises a large current flows between the source and the drain of the MOSFET 33 due to the PWM control signal coming after that occurrence in the first place, whereby temperature of the chip rises. The rise in temperature of the chip is detected by the temperature detecting circuit 35, and the detection output is supplied to the latch circuit 36. Subsequently, the output of the latch circuit 36 is supplied to the gate breaking circuit 37. The gate breaking circuit 37 is controlled by the output of the latch circuit 36 so as to protectively intercept a gate input of the MOSFET 33.

RECEIVED  
DEC - 9 2002  
TECHNOLOGY CENTER 2800

CP/2836  
#4/Amend. A  
Shawn  
12-9-02